

650V N-Channel Enhancement Mode Power MOSFET

MAIN CHARACTERISTICS

I_D	20A
V_{DS}	650V
R_{DS(on)-typ}(@V_{GS}=10V)	<0.46 Ω (Typ:0.38 Ω)

FEATURES

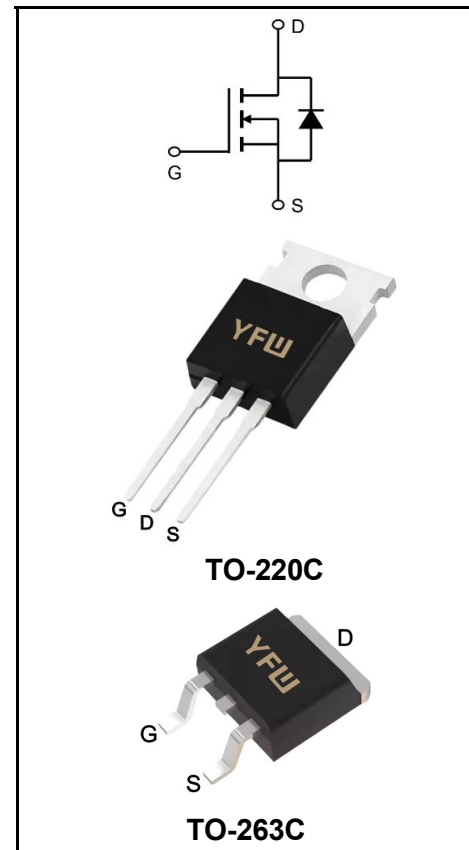
- ♦Fast Switching
- ♦Low ON Resistance
- ♦Low Gate Charge
- ♦100% Single Pulse avalanche energy Test

APPLICATION

- ♦Power switch circuit of adaptor and charge

MECHANICAL DATA

- ♦Case TO-220C/AC TO-263C/ASC
- ♦Mounting Position: Any
- ♦Molded Plastic: UL Flammability Classification Rating 94V-0
- ♦Lead free in compliance with EU RoHS 2011/65/EU directive
- ♦Solder bath temperature 275°C maximum, 10s per JESD 22-B106



Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	650	V
Gate - Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current(note1)	I_{DM}	80	A
Power Dissipation	P_D	250	W
Single Pulse Avalanche Energy(note1)	E_{AS}	700	mJ
Operating Temperature Range	T_J	150	°C
Operating Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction-to-case	R_{θJC}	0.5	°C/W
Thermal Resistance, Junction ambient	R_{θJA}	40	°C/W

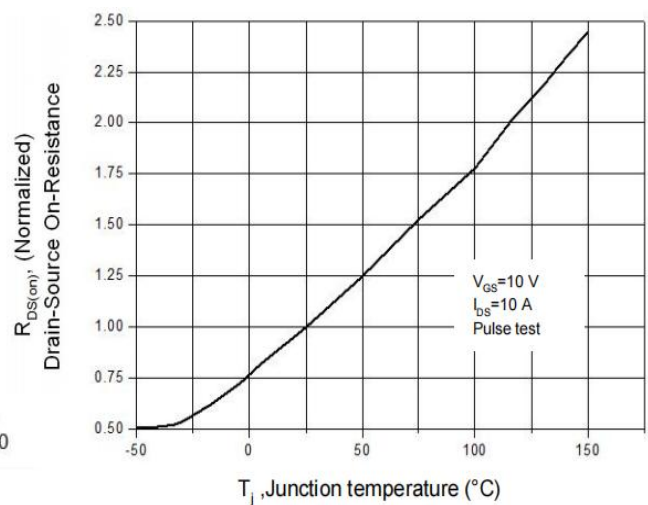
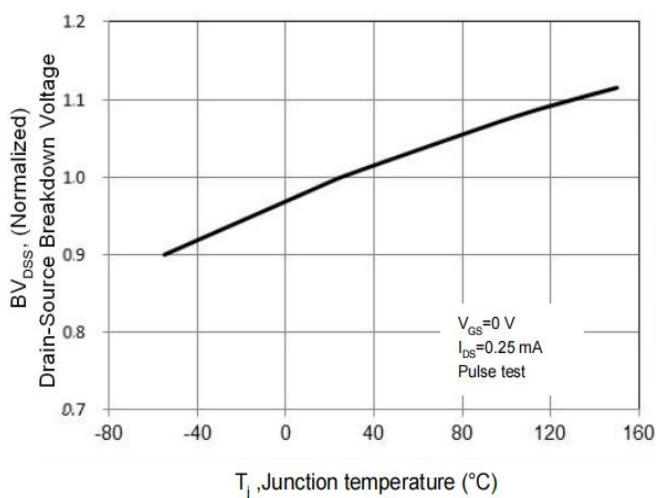
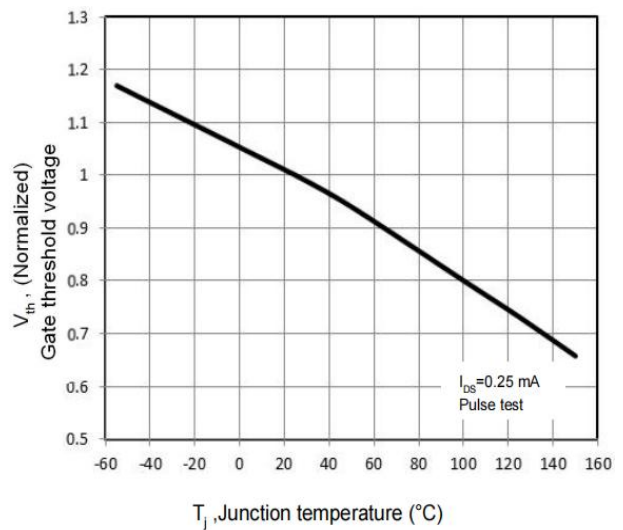
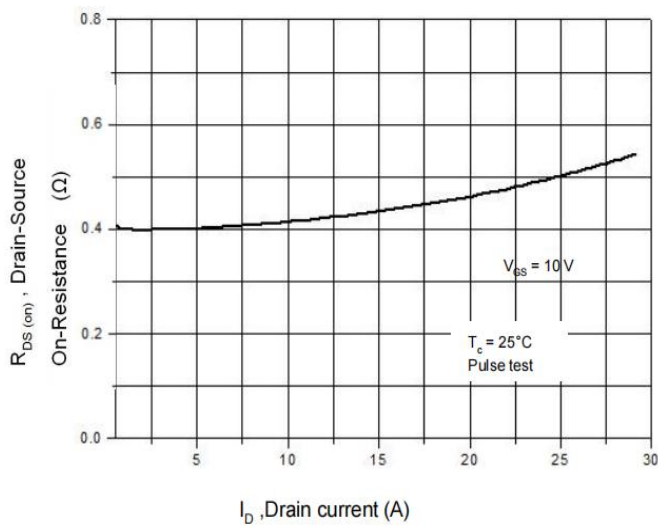
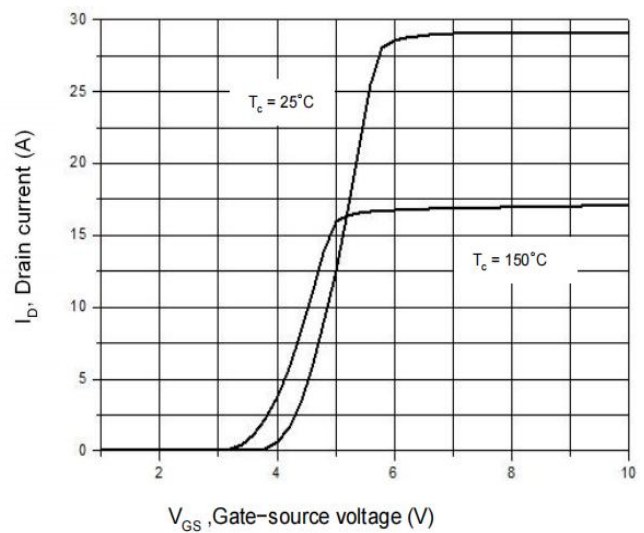
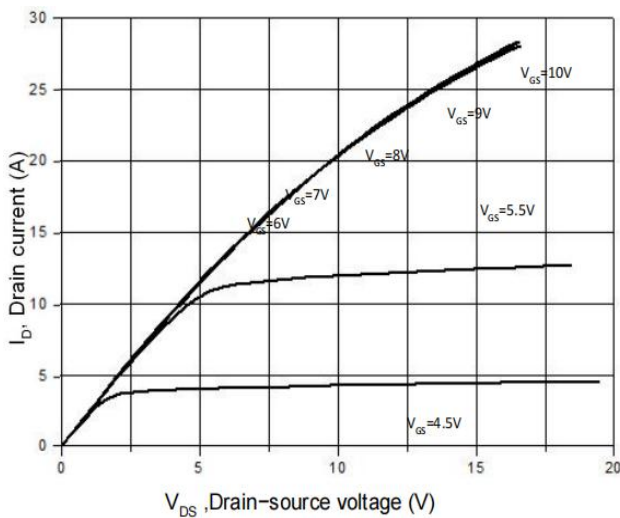
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Maximum Ratings at Tc=25°C unless otherwise specified

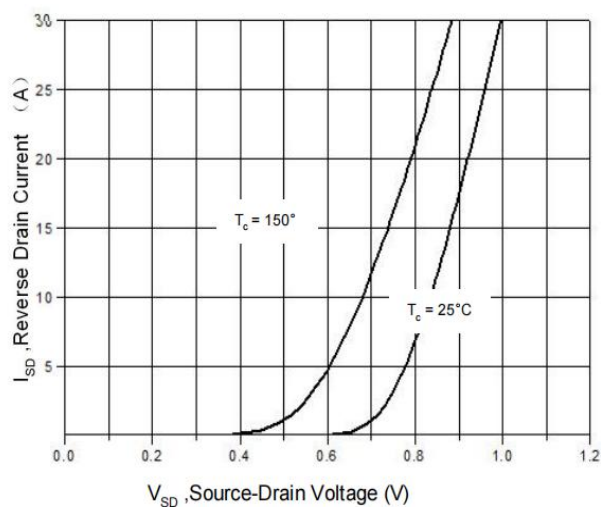
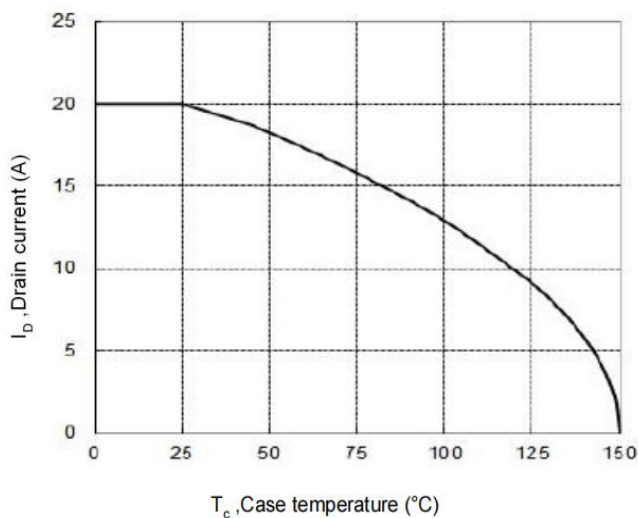
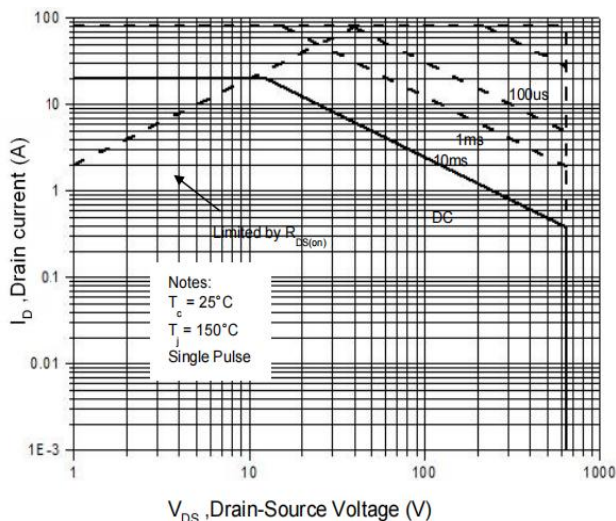
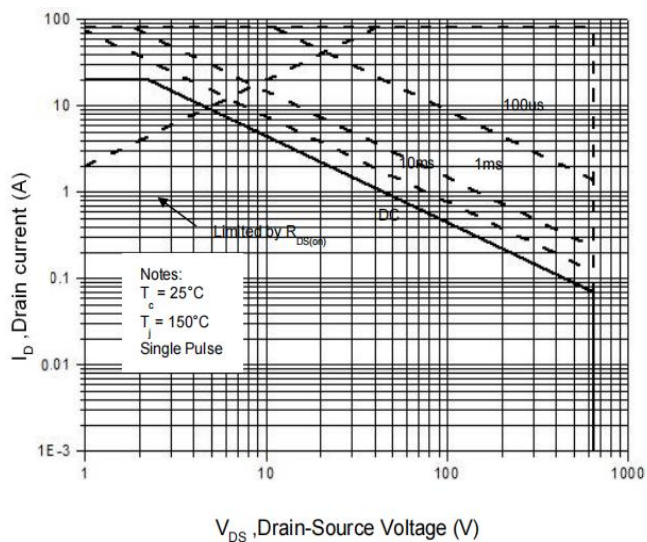
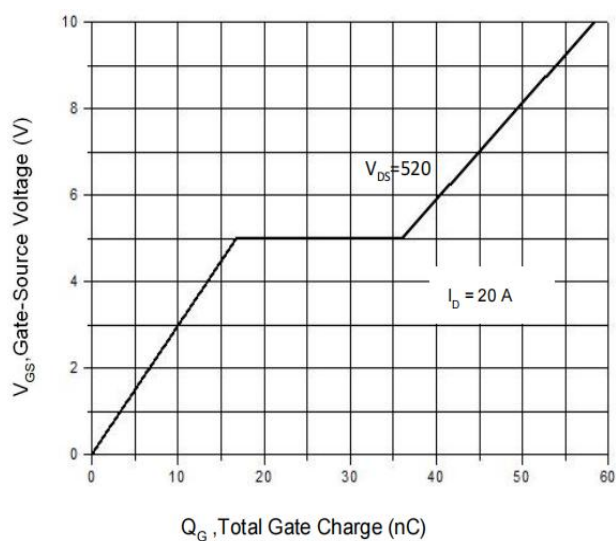
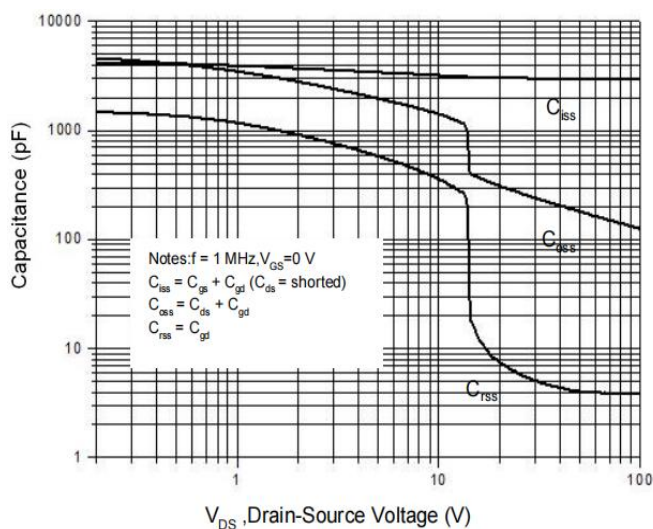
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	650	-	-	V
Drain-Source Leakage Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	$R_{DS(ON)}$	-	0.38	0.46	Ω
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$	g_{fs}	-	18	-	S
Input Capacitance	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 100\text{ KHz}$	C_{iss}	-	3234	-	pF
Output Capacitance		C_{oss}	-	270	-	pF
Reverse Transfer Capacitance		C_{rss}	-	15.6	-	pF
Turn-on Delay Time(Note2)	$I_D = 20\text{ A}$ $V_{DD} = 325\text{ V}$ $R_G = 10\text{ }\Omega$	$t_{d(on)}$	-	21.5	-	ns
Rise Time(Note2)		t_r	-	43	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	97.5	-	ns
Fall Time(Note2)		t_f	-	17.2	-	ns
Total Gate Charge(Note2)	$I_D = 20\text{ A}$ $V_{DD} = 520\text{ V}$ $V_{GS} = 10\text{ V}$	Q_g	-	57.4	-	nC
Gate to Source Charge(Note2)		Q_{gs}	-	16.5	-	nC
Gate to Drain Charge(Note2)		Q_{gd}	-	19	-	nC
Maximun Body-Diode Continuous Current		I_S	-	-	20	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	80	A
Drain-Source Diode Forward Voltage	$I_{SD} = 20\text{ A}$	V_{SD}	-	-	1.5	V
Reverse Recovery Time(Note2)	$I_{SD} = 20\text{ A}, V_{GS} = 0\text{ V},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	492.3	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	7.6	-	μC

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

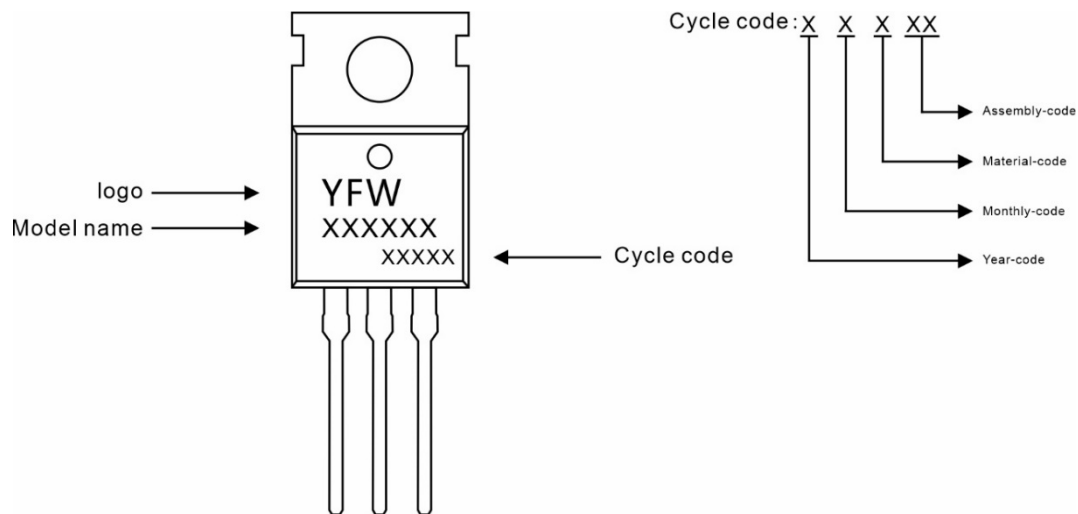
Ratings and Characteristic Curves



Ratings and Characteristic Curves



Marking Diagram



Ordering information

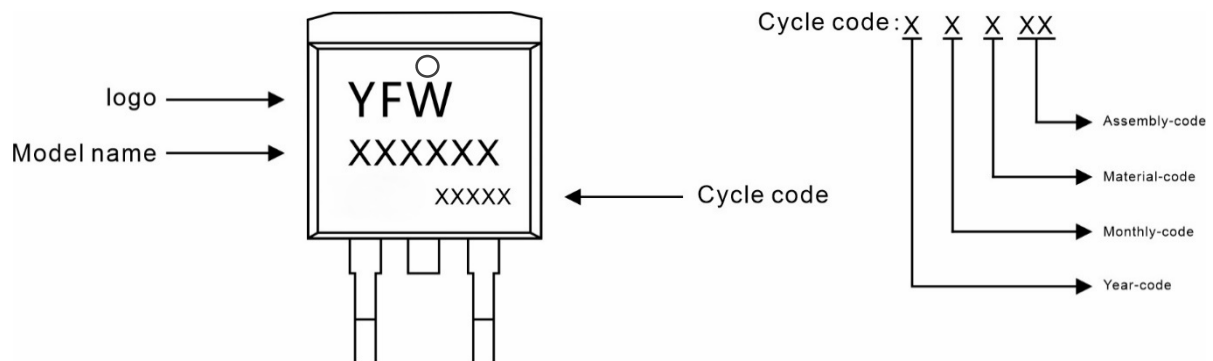
Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW20N65AC	TO-220C	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions

TO-220C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW20N65ASC	TO-263C	0.04oz(1.16g)	800pcs/reel	1600pcs/box 8000pcs/Carton

Package Dimensions

TO-263C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A1	0.00	0.15	0.000	0.006
A2	4.30	4.55	0.169	0.179
B	1.10	1.50	0.043	0.059
b	0.70	0.90	0.028	0.035
b1	1.20	1.50	0.047	0.059
c	0.30	0.60	0.012	0.024
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
L	15.00	15.30	0.591	0.602
L1	5.20	5.40	0.205	0.213
L2	2.40	2.60	0.094	0.102
L3	1.60	1.80	0.063	0.071

Disclaimer

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